

Workshop
“From Epitaxial Materials towards Technological Transfer:
Academic/Industrial meeting”
Paris-Saclay, August 29-31, 2023

August 29, 2023

12h30	Registration
14h00	Welcome & Workshop opening
14h30	<p><i>S1.01 - M. Sawicka - Invited Speaker</i> Porous GaN for nitride laser diodes <i>Institute of High-Pressure Physics, Warsaw - Poland</i></p>
15h00	<p><i>S1.02 - D. H. ÜNAL- The Effect of Layer Thickness on High-Performance MSM Photodetector Structure</i> <i>Sivas Cumhuriyet University, Sivas - Turkey</i></p>
15h15	<p><i>S1.03 - A. Ougazzaden - Invited Speaker</i> Large scale van der Waals Epitaxy and Layer Transfer Techniques of III-nitrides on 2D Boron Nitride - Recent Advances and Applications <i>Georgia tech Metz, Metz - France</i></p>
15h45	Coffee Break
16h30	<p><i>S2.01 - C. Besançon - Invited Speaker</i> III-V integration onto silicon by bonding and regrowth for high-speed telecommunications <i>III-V Lab, a joint lab of Nokia Bell Labs, Thales Research and Technology and CEA LETI, Palaiseau - France</i></p>
17h00	<p><i>S2.02 - A. Adhikari - Bandgap engineering of (Cd, Mg)O ternary alloys for device applications</i> <i>Faculty of Mathematics and Natural Sciences, Cardinal Stefan Wyszyński University, Warsaw - Poland</i></p>
17h15	<p><i>S2.04 - A. Hospodkova - Improved design and technology of AlGaIn/GaN/AlGaIn HEMT structures for high frequency applications</i> <i>Institute of Physics, Prague - Czech Republic</i></p>
17h30	<p><i>S2.05 - G. Afonso - Integration by SAG of multiple SIBH-DFB lasers with optimized performance over >100 nm in the O-band</i> <i>III-V Lab, a joint lab of Nokia Bell Labs, Thales Research and Technology and CEA LETI, Palaiseau - France</i></p>
17h45	<p><i>S2.03 - E. Rosseel - Invited Speaker</i> Epitaxial SiGe/Si Multi-Stacks for Complementary FET Devices <i>Imec, Leuven - Belgium</i></p>
18h15	<p style="text-align: center;">Women in Science & Cocktail Open to Women and Men</p>

August 30, 2023

8h30	Registration
9h00	S3.01 - R. Rousseau - Invited Speaker Advanced optical flux monitoring to control thin layer deposition processes <i>INL-CNRS/Ecole Centrale de Lyon, Ecully - France</i>
9h30	S3.02 - P. Onufrijevs - Comparative Analysis of Nano- and Femtosecond Laser Technologies for GeSn Epilayers: The Potential for IR Device Applications <i>Institute of Technical Physics, Riga Technical University, Riga - Latvia</i>
9h45	S3.03 - B. Beltran-Pitarch - Invited Speaker Micro four-point probe method for the determination of thermal and thermoelectric properties <i>CAPRES – a KLA Company, & DTU Energy, Lyngby - Denmark</i>
10h15	Coffee Break
11h00	S4.01 - G. Gregoire - Invited Speaker Molecular beam epitaxy of III-V materials for infrared applications: from R&D to industrialization <i>III-V Lab, a joint lab of Nokia Bell Labs, Thales Research and Technology and CEA LETI, Palaiseau - France</i>
11h30	S4.02 - N. Ferreira - Ceramic for energy applications prepared by laser technology <i>i3N & Physics Department, Universidade de Aveiro, Aveiro - Portugal</i>
11h45	S4.03 - F. DEPRAT - Invited Speaker Epitaxy for the Heterojunction Bipolar Transistors: Areas for improvement <i>STMicroelectronics, Crolles - France</i>
12h15	Lunch
14h00	S5.01 – W. Braun - Thermal Laser Epitaxy – a universal, high-throughput epitaxy tool <i>Max Planck Institute for Solid State Research, Stuttgart - Germany</i>
14h15	S5.02 - G. Benvenuti - Invited Speaker Chemical Beam Vapour Deposition technique with Sybilla equipment: a review <i>3D-Oxides, Saint-Genis-Pouilly - France</i>
14h45	S5.03 - Z. Jovanovic - PLD growth of functional oxides on rGO-buffered silicon substrate <i>National Institute of the Republic of Serbia, University of Belgrade - Serbia</i>
15h00	S5.04 - S. Rennesson - Invited Speaker MBE growth of GaN-on-Si on 200 mm substrates <i>EasyGaN SAS, Valbonne - France</i>
15h30	S5.05 - E. Chereau - Selective area growth of III-As nanowire arrays by hydride vapour phase epitaxy <i>Institut Pascal, Clermont-Ferrand - France</i>
15h45	S5.06 - C. F. Blanco - Invited Speaker Safe and sustainable-by-design approaches to epitaxial PV cells <i>CML - Institute of Environmental Sciences Faculty of Sciences, Leiden University, Leiden - The Netherlands</i>
16h15	Coffee Break & Poster session
18h00	Academic – Startup/Industrial event – Bar Le 19

August 31, 2023

8h30	Registration
9h00	<p>S6.01 - E. Sandana - Invited Speaker</p> <p>Gallium Oxide: From lab research to space applications</p> <p><i>Nanovation, Châteaufort - France</i></p>
9h30	<p>S7.01 - V. Marinova - Graphene synthesis and applications in liquid crystal tunable phase retarders</p> <p><i>1Institute of Optical Materials and Technologies, Bulgarian Academy of Sciences, Sofia - Bulgaria</i></p>
9h45	<p>S6.03 - R. Bruder - Invited Speaker</p> <p>In situ curvature measurement: a great breakthrough for MBE growth monitoring</p> <p><i>Riber SA, Bezons - France</i></p>
10h15	Coffee Break
11h00	<p>S6.02 - E. Semlali - Growth of GaN nanostructures by HVPE</p> <p><i>Institut Pascal, Clermont-Ferrand - France</i></p>
11h15	<p>S7.02 - S. Sundaram - Invited Speaker</p> <p>Mixed Dimensional Heterostructures on Hexagonal Boron Nitride and its Applications</p> <p><i>Georgia tech Metz, Metz - France</i></p>
11h45	<p>S7.03 - W. Pacuski - Wafer scale molecular beam epitaxy of transition metal dichalcogenides</p> <p><i>Faculty of Physics, University of Warsaw, Warsaw - Poland</i></p>
12h00	<p>S7.04 - J. Brites - Invited Speaker</p> <p>NanoGPS - Facile correlative microscopy for 2D materials flakes, nanowires and epitaxial defects characterization</p> <p><i>HORIBA, Palaiseau - France</i></p>
12h30	End - few words
12h45	Lunch
14h30 - 17h00	C2N-Lab & HORIBA Tours

Poster session – August 30, 2023 – 16h15

PS.01	<p>E. Mensur - Using the Crystallographic Orientation to Enhance the Performance of a Novel Underwater Transducer <i>Gebze Technical University, Dept. of Materials Sci. and Eng, Kocaeli - Turkey</i></p>
PS.02	<p>F. Matos - Engineering ultra-thin films for low noise 2D spintronic sensors <i>INESC Microsistemas e Nanotecnologias, Lisboa - Portugal</i></p>
PS.03	<p>L. Watrin - Study of III-V thin films growth directly on silicon by remote-plasma CVD: Towards a reduction in solar cell industrialization costs <i>Institut Photovoltaïque d'Ile-de-France (IPVF), Palaiseau - France</i></p>
PS.04	<p>R. Bernard - Development of robust, cost efficient and autonomous III-V/Si epitaxial photoelectrochemical cell for H₂ production - NAUTILUS project - PEPR H2 <i>Université Rennes, INSA Rennes, Institut FOTON, Rennes - France</i></p>
PS.05	<p>P. Henning - X-ray photoelectron spectroscopy of partially oxidized ultrathin films of 4d refractory metals deposited by e-beam physical vapor deposition <i>Advanced Epitaxy, Institute of Materials Physics, Georg-August-University of Göttingen - Germany</i></p>
PS.06	<p>B. Napoleonov - Synthesis of MoS₂ nanoclusters by redeposition on a sapphire substrate <i>Institute of Optical Materials and Technologies, Bulgarian Academy of Sciences, Sofia - Bulgaria</i></p>
PS.07	<p>K. Dremluzhenko - Properties of CdTe nanocrystals doped with manganese, cobalt, erbium, and europium <i>V.E. Lashkaryov Institute of Semiconductor Physics NAS of Ukraine, Kyiv - Ukraine</i></p>
PS.08	<p>J. Palakkal - Influence of Epitaxial Relationship and Stoichiometry on the Intrinsic Ferromagnetism of Chromium Tellurides: An Overview <i>Advanced Epitaxy, Institute of Materials Physics, Georg-August-University of Göttingen - Germany</i></p>
PS.09	<p>D. Dimitrov - Low-temperature synthesis of PtTe₂ nanolayer <i>Institute of Solid-State Physics, Bulgarian Academy of Sciences, Sofia - Bulgaria</i></p>
PS.10	<p>A. Khaireh-Walieh - MBE substrate deoxidation surveillance via RHEED image analysis with Deep-Learning <i>LAAS-CNRS, Université de Toulouse, Toulouse - France</i></p>